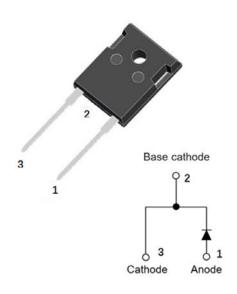






Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	30A
Qc	112.4nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-247AC

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112020NG1
Reverse voltage (repetitive peak) @ T _i =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @T _c =25°C			64
Continuous forward current @T _c =135°C	I _F	Α	30
Continuous forward current @T _c =155°C			20
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160
Power Dissipation@ T _c =25°C		W	306
Power Dissipation@ T₀=110°C	Р _{тот}		132
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	128
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175







■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =20A, T _j =25°C	1.43	1.6
			I _F =20A, T _j =175°C	2.03	2.65
Reverse leakage current	I _R	μА	V _R =1200V, T _j =25°C	4	40
			V _R =1200V, T _j =175°C	93	-
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C , QC = $\int_0^{VR}C(V)dV$	112.4	
Total capacitance	O	pF	V _R =0V, f=1MHZ	1648	-
			V _R =400V, f=1MHZ	106	-
			V _R =800V, f=1MHZ	77	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	29	-

lacktriangleThermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	0.49

■Characteristics (Typical)

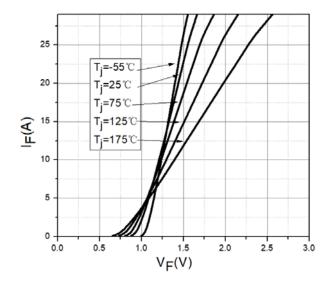


Figure 1. Forward Characteristics

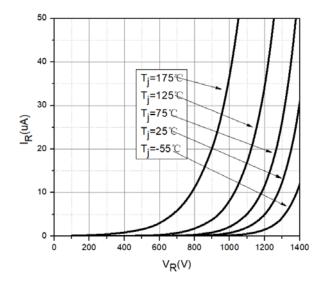


Figure2. Reverse Characteristic

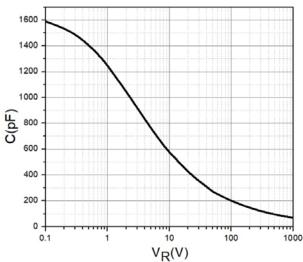


Figure 3. Capacitance vs. Reverse Voltage

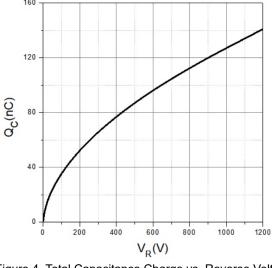


Figure 4. Total Capacitance Charge vs. Reverse Voltage

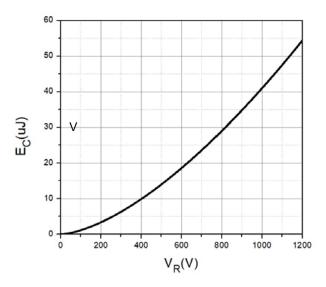


Figure 5. Capacitance Stored Energy

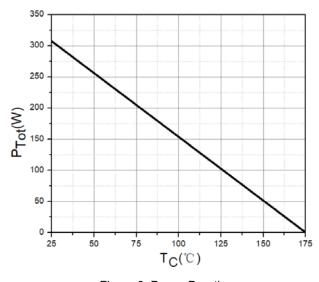
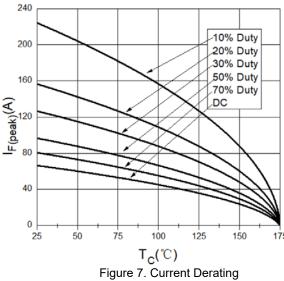


Figure 6. Power Derating



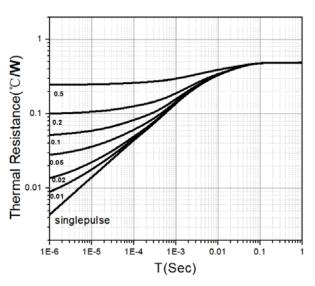


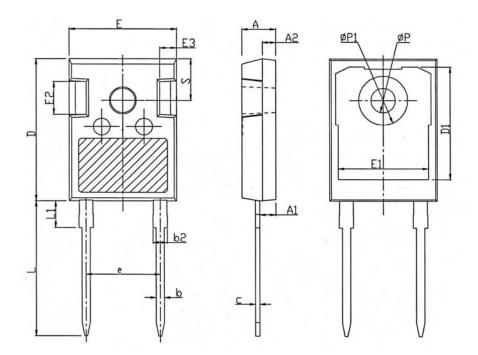
Figure 8. Transient Thermal Impedance







■Outline Dimensions



TO247-AC				
Dim	Min Max			
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
φР	3.40	3.80		
φP1	-	7.30		
S	6.15BSC			



YJD112020NG1



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